Elektronische Bauelemente

B772

PNP Type

Plastic Encapsulate Transistors

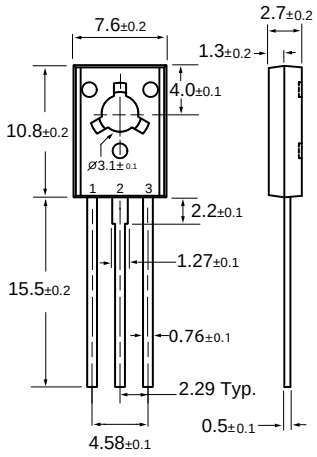
RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

TO-126

Features

* Low speed switching



1: Emitter
2: Collector
3: Base

Dimensions in Millimeters

MAXIMUM RATINGS* T_A=25℃unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current –Continuous	-3	A
P_C	Collector Dissipation	1.25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic=-100μA，I_E=0	-40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -10 mA，I_B=0	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100 μA，I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V，I_E=0			-1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-30 V，I_B=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V，I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -2V, I_C= -1A	60		400	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-2A, I_B= -0.2A			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-2A, I_B= -0.2A			-1.5	V
Transition frequency	f_T	V_{CE}= -5V, I_C=-0.1A f = 10MHz		80		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Characteristics

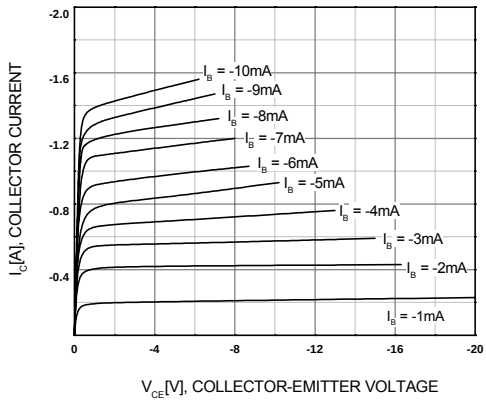


Figure 1. Static Characteristic

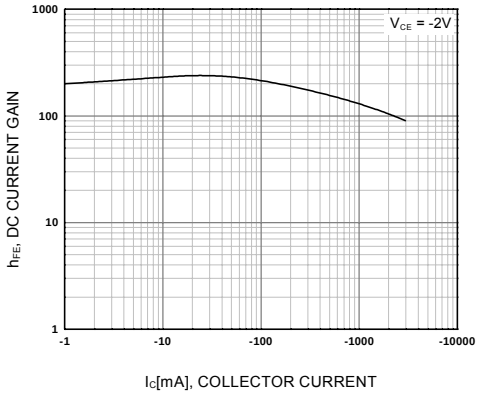


Figure 2. DC current Gain

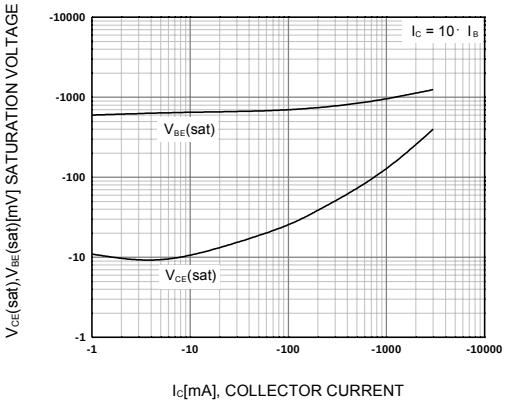


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

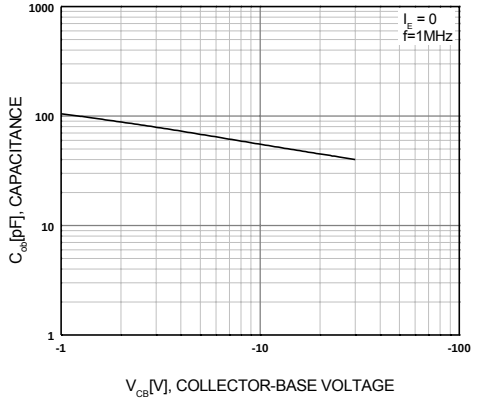


Figure 4. Collector Output Capacitance

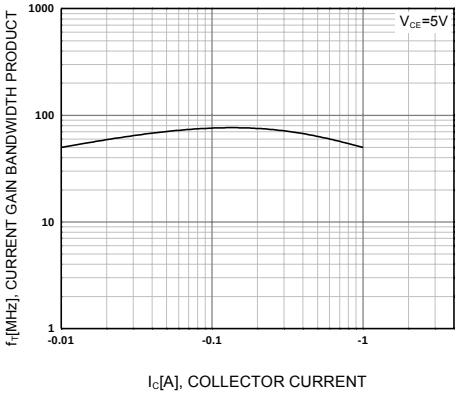


Figure 5. Current Gain Bandwidth Product

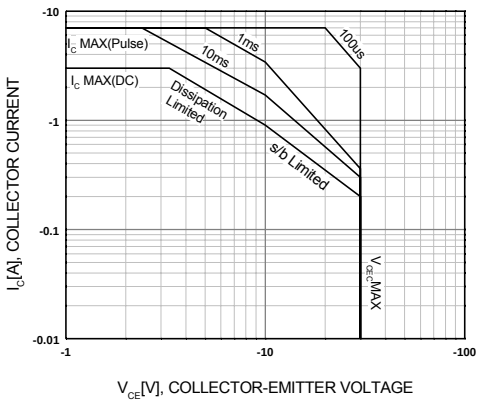


Figure 6. Safe Operating Area